General Description

FSMOS® MOSFET is based on Oriental Semiconductor's unique device design to achieve low $R_{DS(ON)}$, low gate charge, fast switching and excellent avalanche characteristics. The high V_{th} series is specially designed to use in power supply systems with driving voltage of more than 10V.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent reliability and uniformity
- Fast switching and soft recovery

RoHS compliant

Applications

- PD charger
- Motor driver
- Switching voltage regulator
- DC-DC convertor
- Switching mode power supply

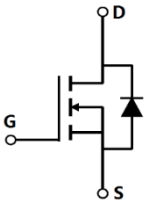
Key Performance Parameters

Parameter	Value	Unit
V_{DS}	60	V
$I_{D,\ pulse}$	960	A
$R_{DS(ON),\ max}$ @ V_{GS}=10V	2.1	mΩ
Q_g	86	nC
PD	200	W

Marking Information

Product Name	Package	Marking
SFS06R019K7NF	TO263-6L	SFS06R019K7N

Package & Pin information



Absolute Maximum Ratings at T_j=25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	60	V
Gate-source voltage	V_{GS}	±20	V
Continuous drain current[1], T_C=25 °C	I_D	250	A
Pulsed drain current[2], T_C=25 °C	$I_{D,\ pulse}$	960	A
Continuous diode forward current[1], T_C=25 °C	I_S	250	A
Diode pulsed current[2], T_C=25 °C	$I_{S,\ pulse}$	960	A
Power dissipation[3], T_C=25 °C	P_D	200	W
Single pulsed avalanche energy[5]	E_{AS}	331	mJ
Operation and storage temperature	T_{stg}, T_j	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.62	°C/W
Thermal resistance, junction-ambient[4]	$R_{\theta JA}$	62	°C/W

Electrical Characteristics at T_j=25°C unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	60			V	V_{GS}=0 V, I_D=250 μA
Gate threshold voltage	$V_{GS(th)}$	2		4	V	V_{DS}=V_{GS}, I_D=250 μA
Drain-source on-state resistance	$R_{DS(ON)}$		1.8	2.1	mΩ	V_{GS}=10 V, I_D=50 A
Gate-source leakage current	I_{GSS}			100	nA	V_{GS}=20 V
				-100		V_{GS}=-20 V
Drain-source leakage current	I_{DSS}			1	μA	V_{DS}=60 V, V_{GS}=0 V
Gate resistance	R_G		1.9		Ω	f=1 MHz, Open drain

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		5580		pF	V_{GS}=0 V, V_{DS}=25 V, f=100 kHz
Output capacitance	C_{oss}		2320		pF	
Reverse transfer capacitance	C_{rss}		92		pF	
Turn-on delay time	$t_{d(on)}$		18		ns	V_{GS}=10 V, V_{DS}=30 V, R_G=2 Ω, I_D=30 A
Rise time	t_r		10		ns	
Turn-off delay time	$t_{d(off)}$		47		ns	
Fall time	t_f		12		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		86		nC	V_{GS}=10 V, V_{DS}=30 V, I_D=30 A
Gate-source charge	Q_{gs}		18		nC	
Gate-drain charge	Q_{gd}		20		nC	
Gate plateau voltage	$V_{plateau}$		3.7		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	I_S=20 A, V_{GS}=0 V
Reverse recovery time	t_{rr}		83		ns	V_R=30 V, I_S=30 A, di/dt=100 A/μs
Reverse recovery charge	Q_{rr}		175		nC	
Peak reverse recovery current	I_{rrm}		3.7		A	

Note

1) Calculated continuous current based on maximum allowable junction temperature.
2) Repetitive rating; pulse width limited by max. junction temperature.
3) Pd is based on max. junction temperature, using junction-case thermal resistance.
4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_a=25 °C.
5) V_{DD}=50 V,V_{GS}=10 V, L=0.3 mH, starting T_j=25 °C.

Electrical Characteristics Diagrams

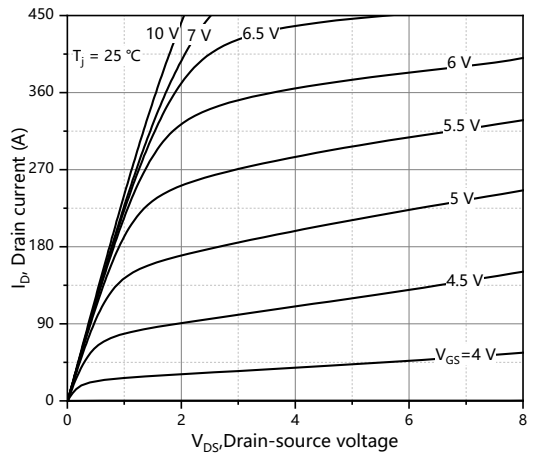


Figure 1. Typ. output characteristics

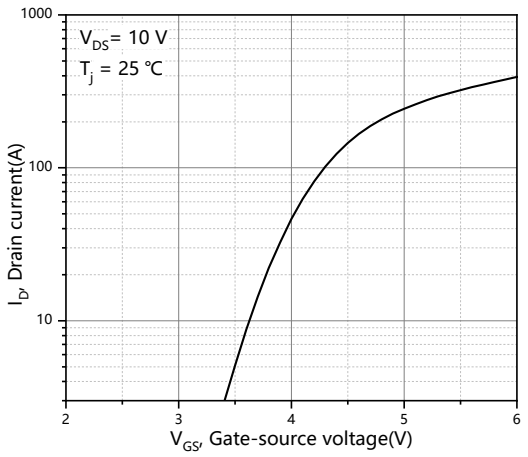


Figure 2. Typ. transfer characteristics

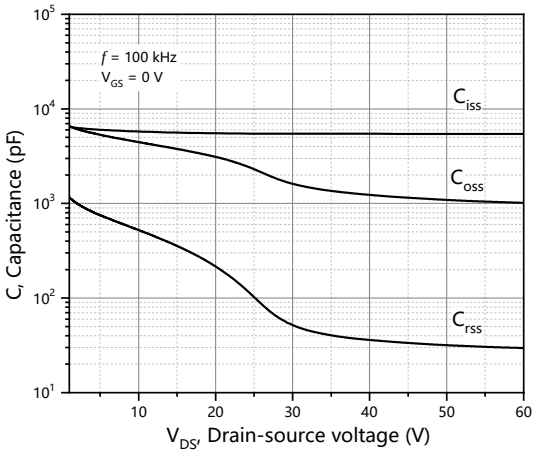


Figure 3. Typ. capacitances

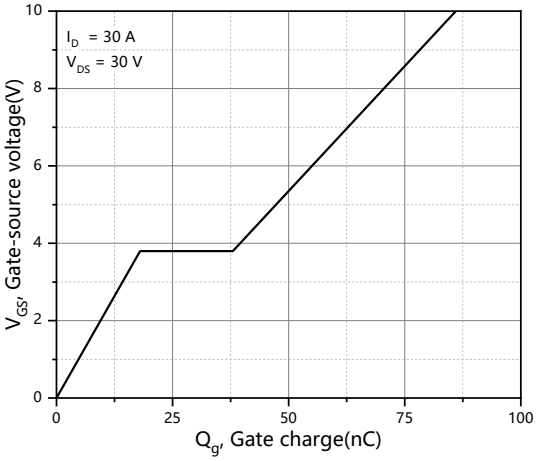


Figure 4. Typ. gate charge

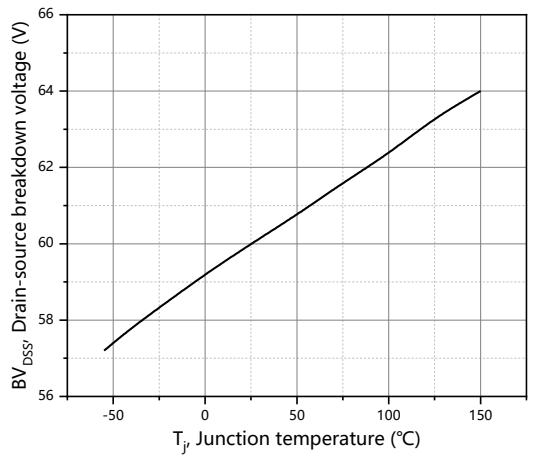


Figure 5. Drain-source breakdown voltage

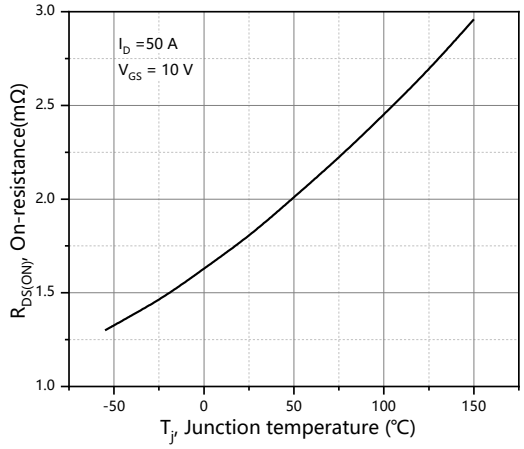


Figure 6. Drain-source on-state resistance

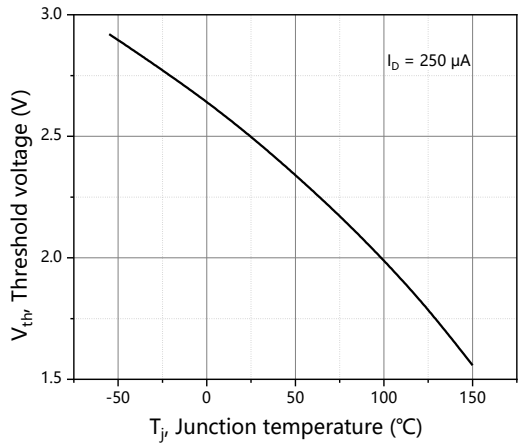


Figure 7. Threshold voltage

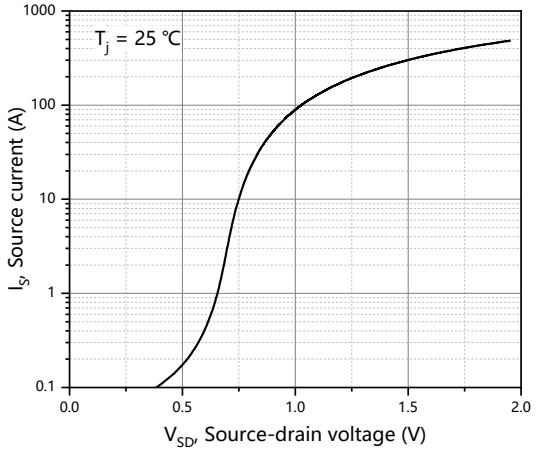


Figure 8. Forward characteristic of body diode

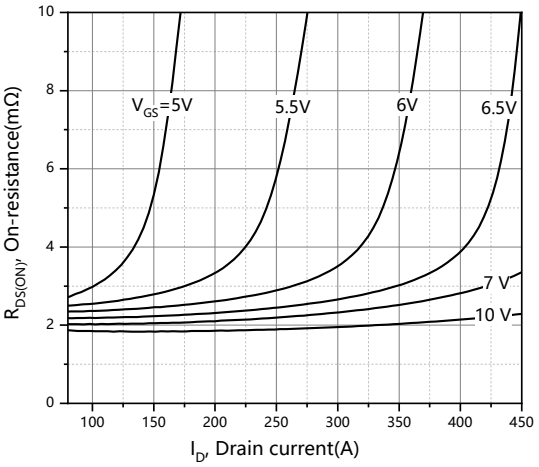


Figure 9. Drain-source on-state resistance

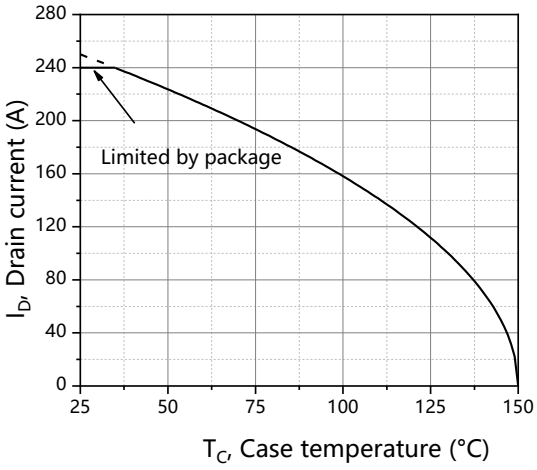


Figure 10. Drain current

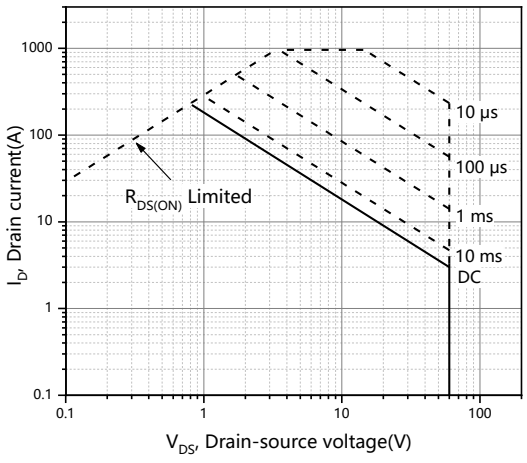


Figure 11. Safe operation area T_C=25 ℃

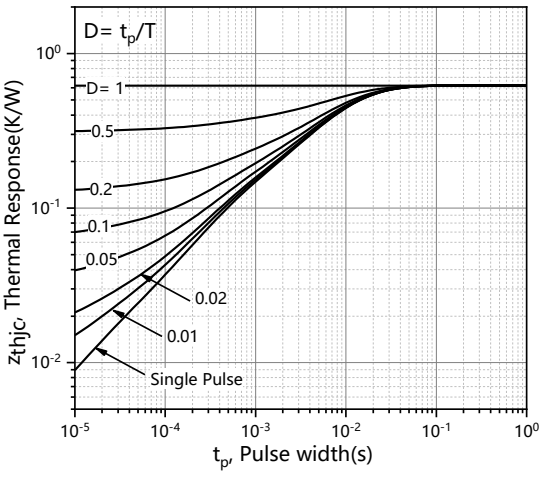


Figure 12. Max. transient thermal impedance

Test circuits and waveforms

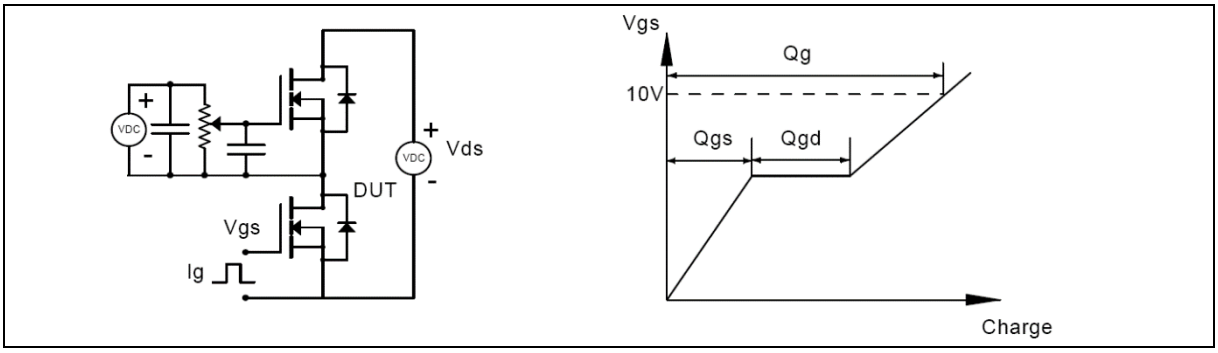


Figure 1. Gate charge test circuit & waveform

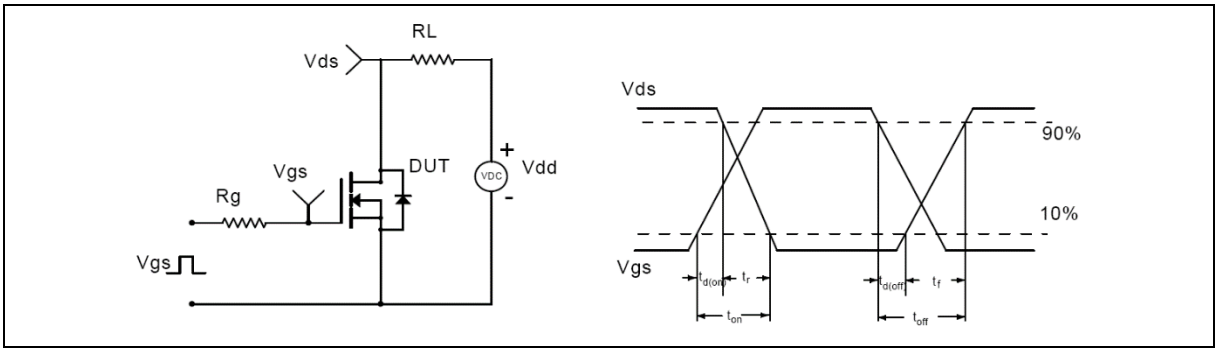


Figure 2. Switching time test circuit & waveforms

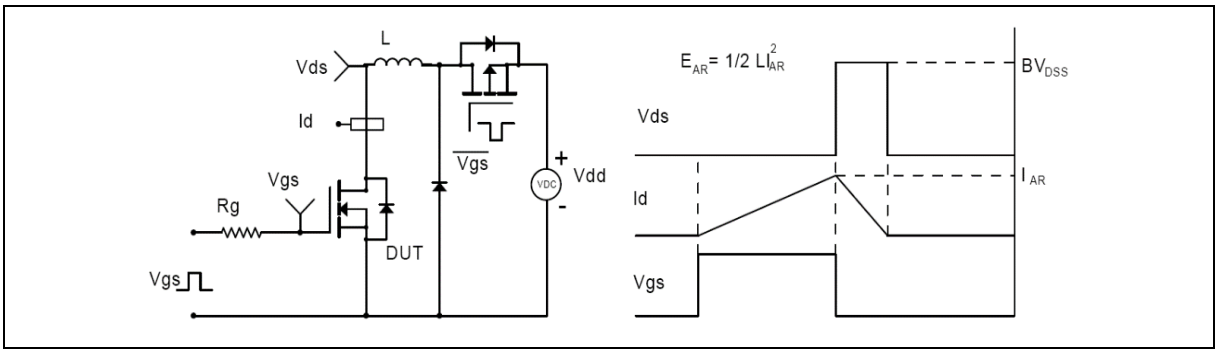


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

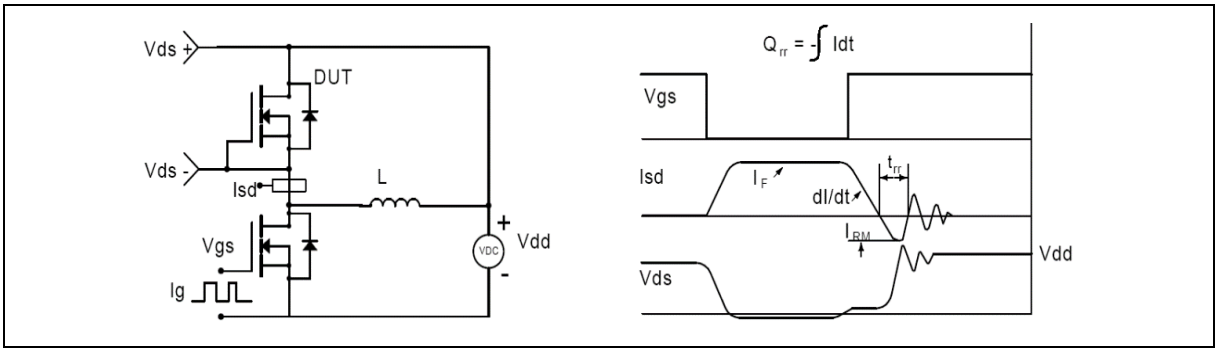
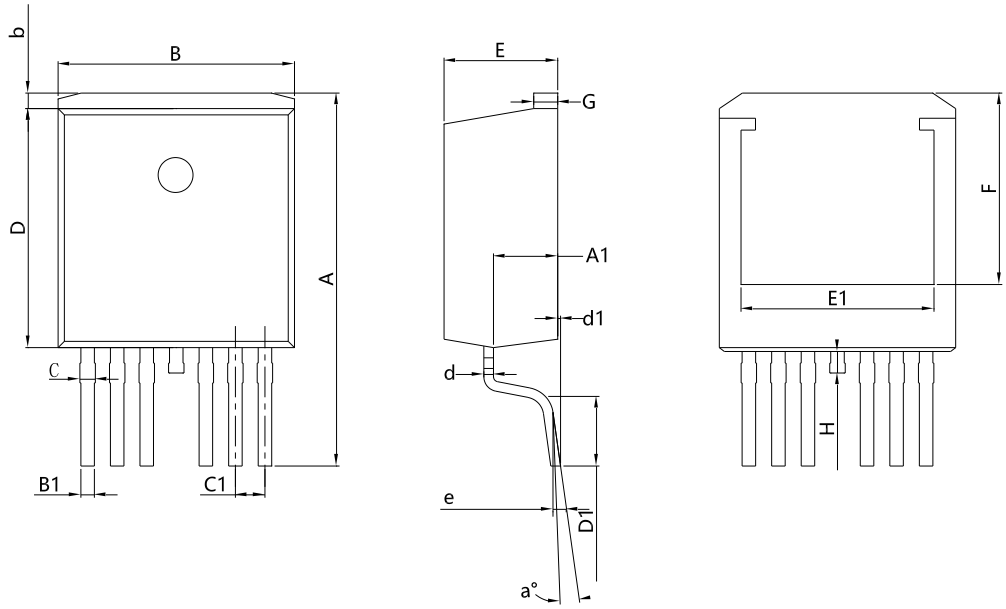


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	14.65	15.00	15.35
A1	2.25	2.40	2.55
B	9.80	10.00	10.20
B1	0.50	0.60	0.70
b	0.80	1.00	1.20
C	0.58	0.68	0.84
C1	1.27 BSC		
D	9.05	9.25	9.45
D1	2.40	2.70	3.00
d	0.40	0.50	0.60
d1	0.01	0.13	0.25
E	4.25	4.40	4.55
E1	7.25	-	-
F	6.90	-	-
e	0.25 BSC		
G	1.20	1.30	1.40
a	2°	5°	8°
H	0.85	1.00	1.15

Version 1: TO263-6L-P package outline dimension

Ordering Information

Package Type	Units/ Reel	Reels/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO263-6L-P	800	1	800	5	4000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
SFS06R019K7NF	TO263-6L	yes	yes	yes

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Revision History

Version	Revision History	Date
V1.0	Initial release	2023-04-25